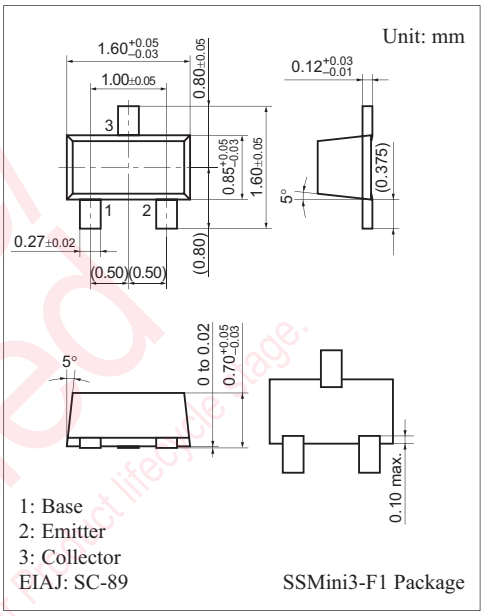
2SD2345J

Silicon NPN epitaxial planar type

For low frequency amplification

■ Features

- High forward current transfer ratio h_{FE}
- Low collector-emitter saturation voltage $V_{CE(sat)}$
- High emitter-base voltage (Collector open) V_{EBO}
- Low noise voltage NV



Marking Symbol: 1Z

■ Absolute Maximum Ratings $T_a = 25°C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	50	V
Collector-emitter voltage (Base open)	V_{CEO}	40	V
Emitter-base voltage (Collector open)	V_{EBO}	15	V
Collector current	I_C	50	mA
Peak collector current	I_{CP}	100	mA
Collector power dissipation	P_C	125	mW
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	−55 to +125	°C

■ Electrical Characteristics $T_a = 25°C \pm 3°C$

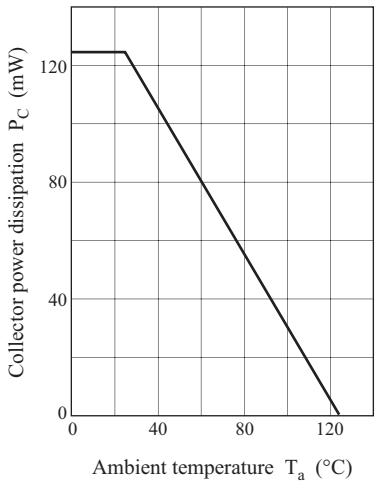
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 10\ \mu A$, $I_E = 0$	50			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 1$ mA, $I_B = 0$	40			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10\ \mu A$, $I_C = 0$	15			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 20$ V, $I_E = 0$			0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 20$ V, $I_B = 0$			1	μA
Forward current transfer ratio *	h_{FE}	$V_{CE} = 10$ V, $I_C = 2$ mA	600		2000	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10$ mA, $I_B = 1$ mA		0.05	0.2	V
Transition frequency	f_T	$V_{CB} = 10$ V, $I_E = -2$ mA, f = 200 MHz		120		MHz

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

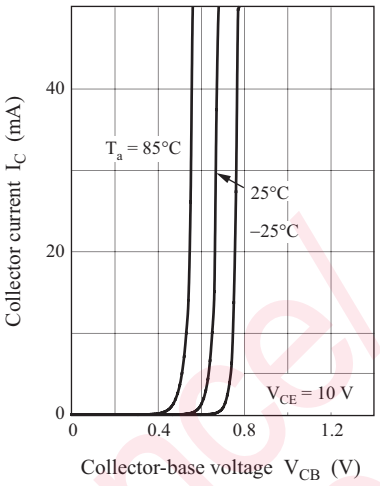
2. *: Rank classification

Rank	S	T
h_{FE}	600 to 1200	1000 to 2000

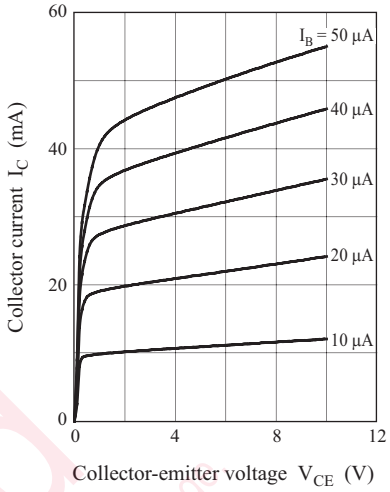
P_C — T_a



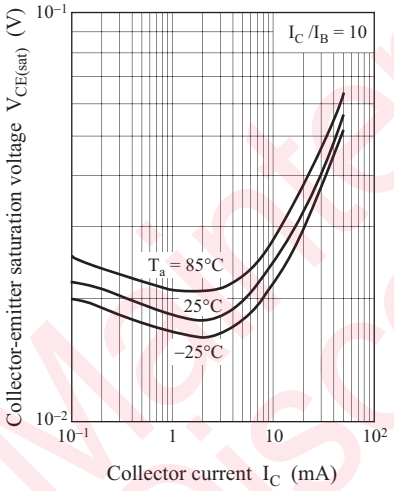
I_C — V_{CB}



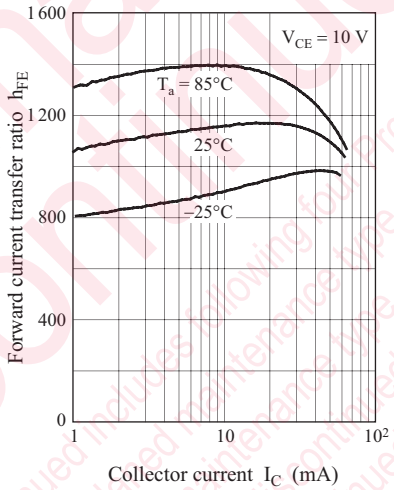
I_C — V_{CE}



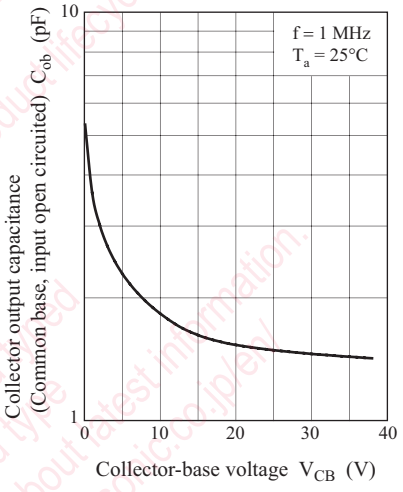
$V_{CE(sat)}$ — I_C



h_{FE} — I_C



C_{ob} — V_{CB}



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